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# Low-Voltage CMOS Quad 2-Input Multiplexer

# With 5 V-Tolerant Inputs (Non-Inverting)

The MC74LCX157 is a high performance, quad 2-input multiplexer operating from a 2.3 to 3.6 V supply. High impedance TTL compatible inputs significantly reduce current loading to input drivers while TTL compatible outputs offer improved switching noise performance. A V<sub>I</sub> specification of 5.5 V allows MC74LCX157 inputs to be safely driven from 5 V devices.

Four bits of data from two sources can be selected using the Select and Enable inputs. The four outputs present the selected data in the true (non-inverted) form. The MC74LCX157 can also be used as a function generator. Current drive capability is 24 mA at the outputs.

#### **Features**

- Designed for 2.3 to 3.6 V V<sub>CC</sub> Operation
- 5 V Tolerant Inputs Interface Capability With 5 V TTL Logic
- LVTTL Compatible
- LVCMOS Compatible
- 24 mA Balanced Output Sink and Source Capability
- Near Zero Static Supply Current (10 μA) Substantially Reduces System Power Requirements
- Latchup Performance Exceeds 500 mA
- ESD Performance:
  - ♦ Human Body Model >2000 V
  - ♦ Machine Model >200 V
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant



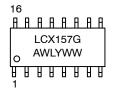
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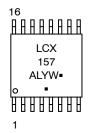


SOIC-16 **D SUFFIX CASE 751B** 





TSSOP-16 **DT SUFFIX** CASE 948F



= Assembly Location

WL, L = Wafer Lot = Year = Work Week = Pb-Free Package

(Note: Microdot may be in either location)

#### **ORDERING INFORMATION**

See detailed ordering and shipping information in the package dimensions section on page 3 of this data sheet.

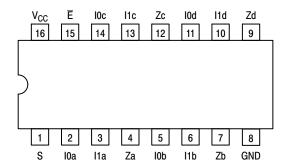


Figure 1. 16-Lead Pinout (Top View)

### **PIN NAMES**

Pins	Function
l0n	Source 0 Data Inputs
l1n	Source 1 Data Inputs
Ē	Enable Input
S	Select Input
Zn	Outputs

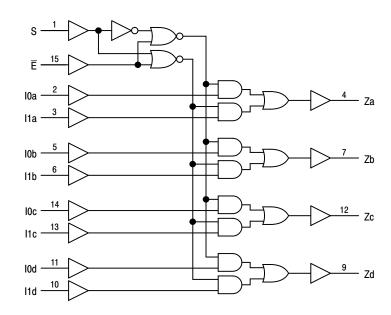


Figure 2. Logic Diagram

# **TRUTH TABLE**

	Inp	uts	Outputs	
Ē	S	I0n	l1n	Zn
H	X	X X	X	L
L L	H	X	H	H
L L	L L	L H	X X	L H

 $H = High \ Voltage \ Level; \ L = Low \ Voltage \ Level; \ X = High \ or \ Low \ Voltage \ Level; \ For \ I_{CC} \ Reasons \ DO \ NOT \ FLOAT \ Inputs$ 

#### **ABSOLUTE MAXIMUM RATINGS**

Symbol	Parameter	Value	Condition	Units
V <sub>CC</sub>	DC Supply Voltage	-0.5 to +7.0		V
VI	DC Input Voltage	$-0.5 \le V_{l} \le +7.0$		V
Vo	DC Output Voltage	$-0.5 \le V_{O} \le V_{CC} + 0.5$	(Note 1)	V
I <sub>IK</sub>	DC Input Diode Current	-50	V <sub>I</sub> < GND	mA
lok	DC Output Diode Current	-50	V <sub>O</sub> < GND	mA
		+50	V <sub>O</sub> > V <sub>CC</sub>	mA
Io	DC Output Source/Sink Current	±50		mA
Icc	DC Supply Current Per Supply Pin	±100		mA
I <sub>GND</sub>	DC Ground Current Per Ground Pin	±100		mA
T <sub>STG</sub>	Storage Temperature Range	-65 to +150		°C
MSL	Moisture Sensitivity		Level 1	

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

1. Output in HIGH or LOW State. Io absolute maximum rating must be observed.

### RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Тур	Max	Units
V <sub>CC</sub>	Supply Voltage Operating Data Retention Only	2.0 1.5	3.3 3.3	3.6 3.6	V
VI	Input Voltage	0		5.5	V
Vo	Output Voltage (HIGH or LOW State)	0		V <sub>CC</sub>	V
I <sub>OH</sub>	HIGH Level Output Current, V <sub>CC</sub> = 3.0 V - 3.6 V			-24	mA
I <sub>OL</sub>	LOW Level Output Current, V <sub>CC</sub> = 3.0 V - 3.6 V			24	mA
I <sub>OH</sub>	HIGH Level Output Current, V <sub>CC</sub> = 2.7 V - 3.0 V			-12	mA
I <sub>OL</sub>	LOW Level Output Current, V <sub>CC</sub> = 2.7 V - 3.0 V			12	mA
T <sub>A</sub>	Operating Free-Air Temperature	-40		+85	°C
Δt/ΔV	Input Transition Rise or Fall Rate, $V_{IN}$ from 0.8 V to 2.0 V, $V_{CC}$ = 3.0 V	0		10	ns/V

# **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
MC74LCX157DR2G	SOIC-16 (Pb-Free)	2500 Tape & Reel
MC74LCX157DTG	TSSOP-16 (Pb-Free)	96 Units / Rail
MC74LCX157DTR2G	TSSOP-16 (Pb-Free)	2500 Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

#### DC ELECTRICAL CHARACTERISTICS

			T <sub>A</sub> = -40°C	to +85°C	
Symbol	Characteristic	Condition	Min	Max	Units
V <sub>IH</sub>	HIGH Level Input Voltage (Note 2)	2.7 V ≤ V <sub>CC</sub> ≤ 3.6 V	2.0		V
V <sub>IL</sub>	LOW Level Input Voltage (Note 2)	2.7 V ≤ V <sub>CC</sub> ≤ 3.6 V		0.8	V
V <sub>OH</sub>	HIGH Level Output Voltage	$2.7 \text{ V} \le \text{V}_{CC} \le 3.6 \text{ V}; \text{I}_{OH} = -100 \mu\text{A}$	V <sub>CC</sub> - 0.2		V
		V <sub>CC</sub> = 2.7 V; I <sub>OH</sub> = -12 mA	2.2		
		V <sub>CC</sub> = 3.0 V; I <sub>OH</sub> = -18 mA	2.4		
		V <sub>CC</sub> = 3.0 V; I <sub>OH</sub> = -24 mA	2.2		
V <sub>OL</sub>	LOW Level Output Voltage	$2.7 \text{ V} \le \text{V}_{CC} \le 3.6 \text{ V}; \text{I}_{OL} = 100 \mu\text{A}$		0.2	V
		V <sub>CC</sub> = 2.7 V; I <sub>OL</sub> = 12 mA		0.4	
		V <sub>CC</sub> = 3.0 V; I <sub>OL</sub> = 16 mA		0.4	
		V <sub>CC</sub> = 3.0 V; I <sub>OL</sub> = 24 mA		0.55	
I <sub>OFF</sub>	Power Off Leakage Current	V <sub>CC</sub> = 0, V <sub>IN</sub> = 5.5 V or V <sub>OUT</sub> = 5.5 V		10	μΑ
I <sub>IN</sub>	Input Leakage Current	V <sub>CC</sub> = 3.6 V, V <sub>IN</sub> = 5.5 V or GND		±5	μΑ
I <sub>CC</sub>	Quiescent Supply Current	V <sub>CC</sub> = 3.6 V, V <sub>IN</sub> = 5.5 V or GND		10	μΑ
$\Delta I_{CC}$	Increase in I <sub>CC</sub> per Input	$2.3 \le V_{CC} \le 3.6 \text{ V}; V_{IH} = V_{CC} - 0.6 \text{ V}$		500	μΑ

<sup>2.</sup> These values of V<sub>I</sub> are used to test DC electrical characteristics only.

# AC CHARACTERISTICS ( $t_R$ = $t_F$ = 2.5 ns; $C_L$ = 50 pF; $R_L$ = 500 $\Omega$ )

				Limits			
			T <sub>A</sub>	= -40°C to +	-85°C		
			V <sub>CC</sub> = 3.0	V to 3.6 V	V <sub>CC</sub> = 2.7 V		
Symbol	Parameter	Waveform	Min	Max	Max	Units	
t <sub>PLH</sub> t <sub>PHL</sub>	Propagation Delay In to Zn	1	1.5 1.5	5.8 5.8	6.3 6.3	ns	
t <sub>PLH</sub> t <sub>PHL</sub>	Propagation Delay S to Zn	1,2	1.5 1.5	7.0 7.0	8.0 8.0	ns	
t <sub>PLH</sub> t <sub>PHL</sub>	Propagation Delay E to Zn	2	1.5 1.5	7.0 7.0	8.0 8.0	ns	
t <sub>OSHL</sub> t <sub>OSLH</sub>	Output-to-Output Skew (Note 3)			1.0 1.0		ns	

<sup>3.</sup> Skew is defined as the absolute value of the difference between the actual propagation delay for any two separate outputs of the same device. The specification applies to any outputs switching in the same direction, either HIGH-to-LOW (t<sub>OSHL</sub>) or LOW-to-HIGH (t<sub>OSLH</sub>); parameter guaranteed by design.

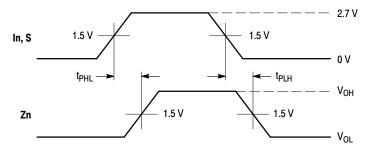
#### **DYNAMIC SWITCHING CHARACTERISTICS**

			T <sub>A</sub> = +25°C			
Symbol	Characteristic	Condition	Min	Тур	Max	Units
V <sub>OLP</sub>	Dynamic LOW Peak Voltage (Note 4)	$V_{CC} = 3.3 \text{ V}, C_L = 50 \text{ pF}, V_{IH} = 3.3 \text{ V}, V_{IL} = 0 \text{ V}$		0.8		V
V <sub>OLV</sub>	Dynamic LOW Valley Voltage (Note 4)	$V_{CC} = 3.3 \text{ V}, C_L = 50 \text{ pF}, V_{IH} = 3.3 \text{ V}, V_{IL} = 0 \text{ V}$		0.8		V

<sup>4.</sup> Number of outputs defined as "n". Measured with "n-1" outputs switching from HIGH-to-LOW or LOW-to-HIGH. The remaining output is measured in the LOW state.

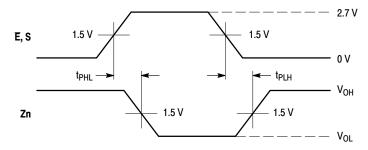
#### **CAPACITIVE CHARACTERISTICS**

Symbol	Parameter	Condition	Typical	Units
C <sub>IN</sub>	Input Capacitance	$V_{CC}$ = 3.3 V, $V_{I}$ = 0 V or $V_{CC}$	7	pF
C <sub>OUT</sub>	Output Capacitance	$V_{CC}$ = 3.3 V, $V_{I}$ = 0 V or $V_{CC}$	8	pF
C <sub>PD</sub>	Power Dissipation Capacitance	10 MHz, $V_{CC}$ = 3.3 V, $V_{I}$ = 0 V or $V_{CC}$	25	pF



### **WAVEFORM 1 - NON-INVERTING PROPAGATION DELAYS**

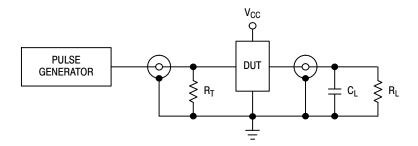
 $t_R$  =  $t_F$  = 2.5 ns, 10% to 90%; f = 1 MHz;  $t_W$  = 500 ns



### **WAVEFORM 2 - INVERTING PROPAGATION DELAYS**

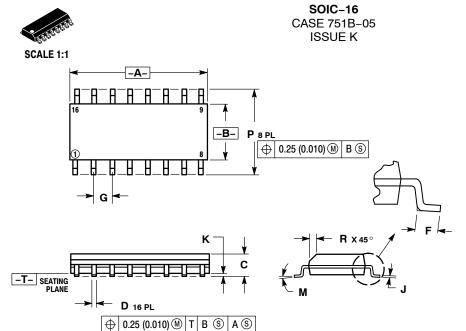
 $t_R$  =  $t_F$  = 2.5 ns, 10% to 90%; f = 1 MHz;  $t_W$  = 500 ns

Figure 3. AC Waveforms



 $C_L$  = 50 pF or equivalent (Includes jig and probe capacitance)  $R_L$  =  $R_1$  = 500  $\Omega$  or equivalent  $R_T$  =  $Z_{OUT}$  of pulse generator (typically 50  $\Omega)$ 

Figure 4. Test Circuit



**DATE 29 DEC 2006** 

- NOTES:
  1. DIMENSIONING AND TOLERANCING PER ANSI
- THE NOTION AND TOLETANOING FER ANSI'Y 14.5M, 1982.
  CONTROLLING DIMENSION: MILLIMETER.
  DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
- PHOI HUSION.

  MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.

  DIMENSION D DOES NOT INCLUDE DAMBAR
  PROTRUSION. ALLOWABLE DAMBAR PROTRUSION

  SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D

  DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIN	IETERS	INC	HES
DIM	MIN	MAX	MIN	MAX
Α	9.80	10.00	0.386	0.393
В	3.80	4.00	0.150	0.157
С	1.35	1.75	0.054	0.068
D	0.35	0.49	0.014	0.019
F	0.40	1.25	0.016	0.049
G	1.27	BSC	0.050	) BSC
J	0.19	0.25	0.008	0.009
K	0.10	0.25	0.004	0.009
M	0°	7°	0°	7°
P	5.80	6.20	0.229	0.244
R	0.25	0.50	0.010	0.019

STYLE 1:		STYLE 2:		STYLE 3:		STYLE 4:			
	COLLECTOR		CATHODE	PIN 1.	COLLECTOR, DYE #1	PIN 1.	COLLECTOR, DY		
2.	BASE		ANODE	2.	BASE, #1	2.	COLLECTOR, #1		
3.	EMITTER	3.	NO CONNECTION	3.	EMITTER, #1	3.	COLLECTOR, #2		
4.	NO CONNECTION	4.	CATHODE	4.	COLLECTOR, #1	4.	COLLECTOR, #2		
5.	EMITTER	5.	CATHODE	5.	COLLECTOR, #2	5.	COLLECTOR, #3		
6.	BASE	6.	NO CONNECTION	6.	BASE, #2	6.	COLLECTOR, #3		
7.	COLLECTOR	7.	ANODE	7.	EMITTER, #2	7.	COLLECTOR, #4		
8.	COLLECTOR	8.	CATHODE	8.	COLLECTOR, #2	8.	COLLECTOR, #4		
9.	BASE		CATHODE	9.	COLLECTOR, #3	9.	BASE, #4		
10.	EMITTER		ANODE	10.	BASE, #3	10.	EMITTER, #4		
11.	NO CONNECTION		NO CONNECTION	11.	EMITTER, #3	11.	BASE, #3		
12.	EMITTER		CATHODE	12.	COLLECTOR, #3	12.	EMITTER, #3		
13.	BASE		CATHODE	13.	COLLECTOR, #4	13.	BASE, #2	SOI DEE	RING FOOTPRINT
14.	COLLECTOR		NO CONNECTION	14.	BASE, #4	14.	EMITTER, #2	SOLDER	IIIIG FOOTFRINT
15.	EMITTER			15.	EMITTER, #4	15.	BASE, #1		8X
16.	COLLECTOR	16.	CATHODE	16.	COLLECTOR, #4	16.	EMITTER, #1	<b>—</b>	— 6.40 — <del>&gt;</del>
									0.10
STYLE 5:		STYLE 6:		STYLE 7:					16X 1.12 ✓ ➤
PIN 1.	DRAIN, DYE #1		CATHODE	PIN 1.	SOURCE N-CH				
2.	DRAIN, #1		CATHODE	2.	COMMON DRAIN (OUTPUT	7)		. $\Box$ 1	16
3.	DRAIN, #2	3.	CATHODE	3.	COMMON DRAIN (OUTPUT			<b>,</b> — ·	
4.	DRAIN, #2	4.	CATHODE	4.	GATE P-CH	,			
5.	DRAIN, #3	5.	CATHODE	5.	COMMON DRAIN (OUTPUT	7)		16X 🛣	
6.	DRAIN, #3		CATHODE	6.	COMMON DRAIN (OUTPUT			.58 J	' <u> </u>
7.	DRAIN, #4		CATHODE	7.	COMMON DRAIN (OUTPUT		U		1
8.	DRAIN, #4	8.	CATHODE	8.	SOURCE P-CH	,			
9.	GATE, #4	9.	ANODE	9.	SOURCE P-CH				
10.	SOURCE, #4	10.	ANODE	10.	COMMON DRAIN (OUTPUT	7)			
11.	GATE, #3	11.	ANODE	11.	COMMON DRAIN (OUTPUT				
12.	SOURCE, #3	12.	ANODE	12.	COMMON DRAIN (OUTPUT				
13.	GATE, #2	13.	ANODE	13.	GATE N-CH	,			
14.	SOURCE, #2	14.	ANODE	14.	COMMON DRAIN (OUTPUT	7)			— ↓ PITCH
15.	GATE, #1	15.	ANODE	15.	COMMON DRAIN (OUTPUT				<u> </u>
16.	SOURCE, #1		ANODE	16.	SOURCE N-CH	,			
	/""		-					□ <sub>8</sub>	9 +
								۰	<b>,</b>
									DIMENSIONS: MILLIMETERS

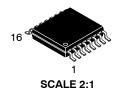
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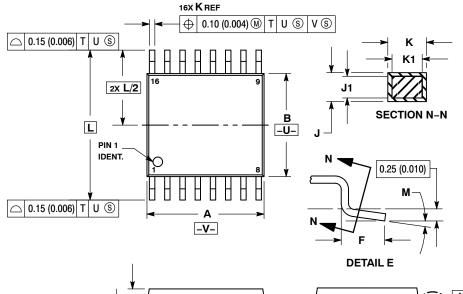
D

-T- SEATING PLANE



TSSOP-16 CASE 948F-01 ISSUE B

**DATE 19 OCT 2006** 



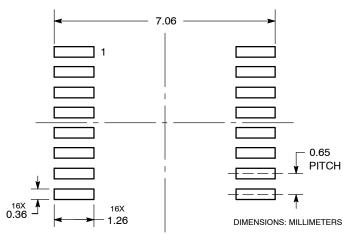
#### NOTES

- JIES:
  DIMENSIONING AND TOLERANCING PER
  ANSI Y14.5M, 1982.
  CONTROLLING DIMENSION: MILLIMETER.
  DIMENSION A DOES NOT INCLUDE MOLD
  FLASH. PROTRUSIONS OR GATE BURRS.
  MOLD EL ROLL OF GATE BURDS SUAL NO.
- MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
  DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION.
  INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
- DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION. TERMINAL NUMBERS ARE SHOWN FOR
- REFERENCE ONLY.
- DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α	4.90	5.10	0.193	0.200
В	4.30	4.50	0.169	0.177
C		1.20		0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65 BSC		0.026 BSC	
Н	0.18	0.28	0.007	0.011
7	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
Ы	6.40 BSC		0.252 BSC	
М	0 °	8 °	0 °	8 °

### **SOLDERING FOOTPRINT**

G



#### **GENERIC MARKING DIAGRAM\***



XXXX = Specific Device Code Α = Assembly Location

= Wafer Lot L Υ = Year W = Work Week = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

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